

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MDS500L

500 Watts, 50 Volts, Pulsed Avionics 1030 - 1090 MHz

GENERAL DESCRIPTION

The MDS500L is a high power COMMON BASE bipolar transistor. It is designed for MODE-S ELM systems in the 1030 - 1090 MHz frequency band. The transistor includes input and output prematch for broadband performance. The device has gold thin-film metallization and diffused ballasting in a hermetically sealed package for proven highest MTTF.

CASE OUTLINE 55ST Style 1

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

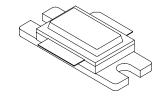
Device Dissipation @25°C¹ 833 W

Maximum Voltage and Current

Collector to Emitter Voltage (BV_{ces}) 70 V Emitter to Base Voltage (BV_{ebo}) 3.5 V Peak Collector Current (I_c) 24 A

Maximum Temperatures

Storage Temperature $-65 \text{ to } +150 \text{ }^{\circ}\text{C}$ Operating Junction Temperature $+200 \text{ }^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 1030, 1090 MHz	500			W
P_{in}	Power Input	Vcc = 50 Volts			60	W
P_{g}	Power Gain	PW = Note 2	9.2			dB
η_c	Collector Efficiency	DF = Note 2		50		%
VSWR	Load Mismatch Tolerance				2:1	
Pd^1	Pulse Droop				0.8	dB
Trise ¹	Rise Time				100	nSec

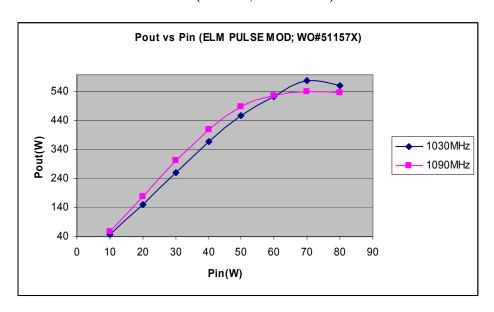
FUNCTIONAL CHARACTERISTICS @ 25°C

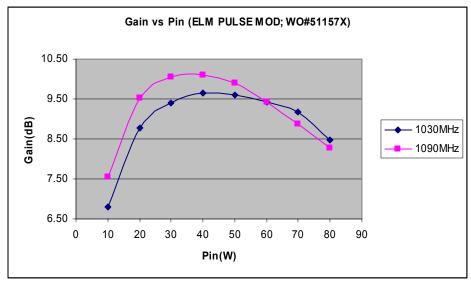
$\mathrm{BV}_{\mathrm{ebo}}$	Emitter to Base Breakdown	Ie = 15 mA	3.0		V
BV_{ces}	Collector to Emitter Breakdown	Ic = 50 mA	70		V
$\mathrm{BV}_{\mathrm{cbo}}$	Collector to Base Breakdown	Ic = 50 mA	70		V
Ices	Collector to Emitter Leakage	Vce = 50V		15	mA
h_{FE}	DC – Current Gain	Vce = 5V, Ic = 1.0 A	20		
θjc ¹	Thermal Resistance			0.08	°C/W

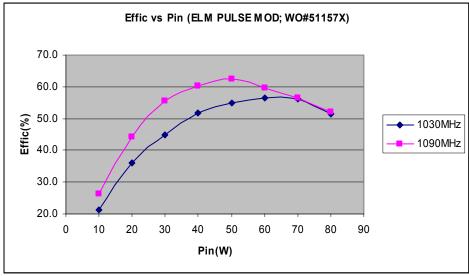
NOTE 1: AT RATED OUTPUT POWER AND PULSE CONDITIONS NOTE 2: ELM Burst: 32µSec ON/ 18µSec OFF x 48, repeated at 23mSec

REV C - March 2008

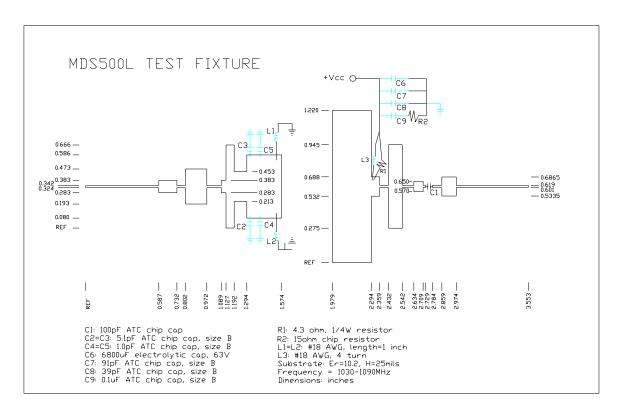
MDS500L SAMPLE RF DATA (SN#7-23; WO#51157X)





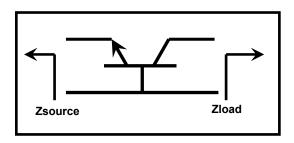


Microsemi reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at www.microsemi.com or contact our factory direct.



IMPEDANCE DATA

FREQUENCY	$Z_{\text{source}}(\text{ohms})$	Z _{load} (ohms)		
1030	1.90 – j1.60	1.79 – j1.51		
1090	2.10 - j1.61	2.05 – j1.76		
1150	2.26 - i1.82	2.21 - j2.21		



MDS500L

